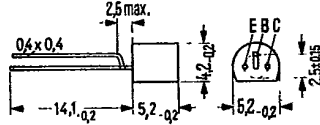


SIEMENS AKTIENGESELLSCHAFT 1 D _____

BF 562 is an NPN silicon RF transistor in TO 92 plastic package (10 A 3 DIN 41868).
 The transistor is particularly suitable for controllable VHF input stages in TV tuners.

Type	Ordering code
BF 562	Q62702-F542



Mounting instruction: Fixing hole dia 0.6
 Approx. weight 0.25 g Dimensions in mm

Maximum ratings ($T_{amb} = 25^{\circ}\text{C}$)

Collector-emitter voltage	V_{CEO}	20	V
Collector-base voltage	V_{CBO}	30	V
Emitter-base voltage	V_{EBO}	3	V
Collector current	I_C	20	mA
Junction temperature	T_j	150	$^{\circ}\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^{\circ}\text{C}$
Total power dissipation ($T_{amb} \leq 45^{\circ}\text{C}$)	P_{tot}	250	mW

Thermal resistance

Junction to ambient air	R_{thJA}	≤ 420	K/W
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Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Base current ($I_C = 3 \text{ mA}; V_{CE} = 10 \text{ V}$)	I_B	≤ 150	μA
($I_C = 10 \text{ mA}; V_{CE} = 7 \text{ V}$)	I_B	≤ 2	mA
Collector-emitter breakdown voltage ($I_C = 1 \text{ mA}$)	$V_{(BR)CEO}$	≥ 20	V
Collector-base breakdown voltage ($I_C = 10 \mu\text{A}$)	$V_{(BR)CBO}$	≥ 30	V
Emitter-base breakdown voltage ($I_E = 10 \mu\text{A}$)	$V_{(BR)EBO}$	≥ 3	V

Dynamic characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Transition frequency ($I_C = 2.5 \text{ mA}; V_{CE} = 10 \text{ V}; f = 100 \text{ MHz}$)	f_T	600	MHz
Power gain ($I_C = 2.5 \text{ mA}; V_{CE} = 10 \text{ V}; f = 200 \text{ MHz};$ $R_g = 60 \Omega; R_L = 920 \Omega$)	G_{pb}	16	dB
Noise figure ($I_C = 2.5 \text{ mA}; V_{CE} = 10 \text{ V}; f = 200 \text{ MHz};$ $R_g = 60 \Omega$)	NF	3	dB
Reverse transfer capacitance ($I_C = 1 \text{ mA}; V_{CE} = 10 \text{ V}; f = 1 \text{ MHz}$)	$-C_{12e}$	0.65	pF
Reverse transfer capacitance ($V_{BE} = 0; V_{CB} = 10 \text{ V}; f = 1 \text{ MHz}$)	$-C_{12b}$	0.12	pF